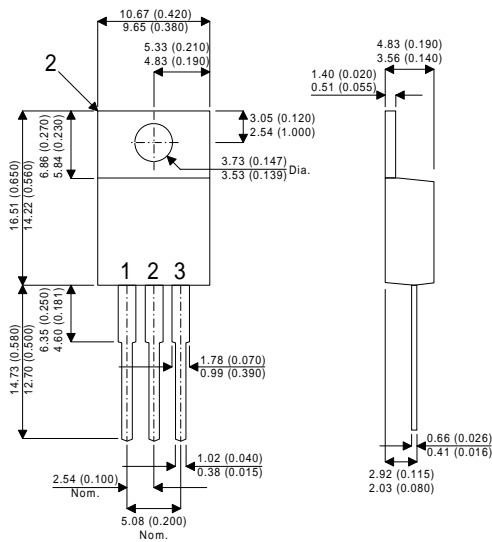


TO220-AC Package Outline.
Dimensions in mm (inches)



**N-CHANNEL
ENHANCEMENT MODE
HIGH VOLTAGE
ISOLATED
POWER MOSFETS**

V_{DSS} 1500V
 $I_{D(cont)}$ 0.1A
 $R_{DS(on)}$ 140Ω

Pin 1 – Gate Pin 2 – Drain Pin 3 – Source

ABSOLUTE MAXIMUM RATINGS ($T_{AMB} = 25^{\circ}C$ unless otherwise stated)

V_{DSS}	Drain – Source Voltage	1500	V
I_D	Continuous Drain Current	0.1	A
I_{DM}	Pulsed Drain Current	0.2	A
V_{GS}	Gate – Source Voltage	±20	V
P_D	Total Power Dissipation	20	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

ELECTRICAL CHARACTERISTICS ($T_{AMB} = 25^{\circ}C$ unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	1500			V
$R_{DS(ON)}$	Drain – Source On State Resistance	$V_{GS} = 10V, I_D = 50mA$		140	200	Ω
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200V, V_{GS} = 0V$			100	μA
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			±100	nA
$V_{GS(off)}$	Cutoff Voltage	$V_{DS} = 10V, I_D = 1.0mA$	1.5		3.5	V
C_{iss}	Input Capacitance	$V_{DS} = 20V$ $f = 1MHz$		40		pF
C_{oss}	Output Capacitance			12		
C_{rss}	Reverse Transfer Capacitance			3.0		
t_{on}	Turn-on Time	$V_{GS} = 10V$		40		ns
t_{off}	Turn-off Time	$I_D = 50mA$		400		
V_{SD}	Diode Forward Voltage	$V_{GS} = 0, I_S = 0.1A$		1.0	1.5	V
$ Y_{FS} $	Forward Transfer Admittance	$V_{DS} = 20V, I_D = 50mA$	50	100		mS